## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

RAJARAM BHAT, et al

Examiner:

Serial No:

Group Art Unit:

Filed:

For:

**GROWTH OF DILUTE NITRIDE** 

COMPOUNDS

## INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §§ 1.56, 1.97 – 1.98

Commissioner of Patents Alexandria, VA 22313-1450

Dear Sir:

The Examiner's attention is hereby directed to the following reference(s) listed on the attached Form PTO-1449 for consideration in connection with the examination of the above-identified patent application. One copy of the non-US reference(s) is enclosed.

This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that each or all of the enclosed documents constitute "prior art." If it should be determined that any of the submitted documents do not constitute "prior art" under United States law, applicant(s) reserve the right to present to the office the relevant facts and law regarding the appropriate status of such documents.

Applicant(s) further reserve the right to take appropriate action to establish the patentability of the disclosed invention over the enclosed references, should one or more of the references be applied against the claims of the present application.

Respectfully submitted,

Jyllana Agon

Registration No. 33,468

Corning Incorporated

SP-TI-03-1

Corning, NY 14831

607-974-6574

Date: 1/21 /D

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner of Patents, Alexandria, Va 22313-1450 on

Date of Deposit

Juliana Agon
Name of applicant, assignee, or

Name of applicant, assignee, or Registered Representative

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Date of Signatur

EXPRESS MAIL NO. EV 327190350 US

Revision: August 30, 2002

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FORM PTO-1449 (MODIFIED)					ATTORNEY DOCKET NO.			SERIAL NO.			
LIST OF PATENTS AND PUBLICATIONS				SP03-165							
FOR APPLICANTS INFORMATION DISCLOSURE STATEMENT				APPLICANT RAJARAM BHAT, et al.							
					FILING DATE			GROUP:			
REFERE	NCE D	ESIGNATION		U.S	S. PATENT and PUBLICA	TION :	DO	CUMEN'	TS		
Examiner Initial		Document Number	Date	e	Name	Clas	ss	Sub- Class		g Date pprop.	
	AA	2002/0085973A1	7/4/02	2	Park	423		351			
	AB	5,689,123	11/18	/97	Major, et al	257		190			
	AC	5,891,790	4/6/99	•	Keller, et al	438		508			
	AD	5,944,913	3 8/31/9		Hou	136		255			
	AE	6,046,096	4/4/00	)	Ouchi	438		510			
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	AJ					438	38 962				
	AK										
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	AM	"Room Temperature Operation of GaInNAs/GaInP Double-Heterostructure Laser Diodes Grown by Metalorganic Chemical Vapor Deposition", Sato, et al Jpn. J. Appl. Phys. Vo. 36 1997 pp 2671-2675									
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	AO										
	AP										
	AQ										
	AR	"Structural characterization of a dimeric dimethylindium azide and its use as a single-source precursor for InN thin films", Bae, et al J. of Organic Metallic Chemistry 616(2000) 128-134									
AS "Preparation of Phase-Pure InSe Thin Films by MOCVD Using a New Single-Source Preparation											

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[(Me)<sub>2</sub>In(μ-SeMe)]<sub>2</sub>, Cho, et al Bull. Korean Chem. Soc. 2003 Vol. 24, No. 5 645-646

DATE CONSIDERED:

**EXAMINER:**